

NTMD6P02, NVMD6P02

Power MOSFET

6 A, 20 V, P-Channel SOIC-8, Dual

Features

- Ultra Low $R_{DS(on)}$
- Higher Efficiency Extending Battery Life
- Logic Level Gate Drive
- Miniature Dual SOIC-8 Surface Mount Package
- Diode Exhibits High Speed, Soft Recovery
- Avalanche Energy Specified
- These Devices are Pb-Free and are RoHS Compliant
- NVMD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

Applications

- Power Management in Portable and Battery-Powered Products, i.e.: Cellular and Cordless Telephones, and PCMCIA Cards

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	-20	V
Gate-to-Source Voltage – Continuous	V_{GS}	± 12	V
Thermal Resistance – Junction-to-Ambient (Note 1)	$R_{\theta JA}$	62.5	$^{\circ}\text{C/W}$
Total Power Dissipation @ $T_A = 25^{\circ}\text{C}$	P_D	2.0	W
Continuous Drain Current @ $T_A = 25^{\circ}\text{C}$	I_D	-7.8	A
Continuous Drain Current @ $T_A = 70^{\circ}\text{C}$	I_D	-5.7	A
Maximum Operating Power Dissipation	P_D	0.5	W
Maximum Operating Drain Current	I_D	-3.89	A
Pulsed Drain Current (Note 4)	I_{DM}	-40	A
Thermal Resistance – Junction-to-Ambient (Note 2)	$R_{\theta JA}$	98	$^{\circ}\text{C/W}$
Total Power Dissipation @ $T_A = 25^{\circ}\text{C}$	P_D	1.28	W
Continuous Drain Current @ $T_A = 25^{\circ}\text{C}$	I_D	-6.2	A
Continuous Drain Current @ $T_A = 70^{\circ}\text{C}$	I_D	-4.6	A
Maximum Operating Power Dissipation	P_D	0.3	W
Maximum Operating Drain Current	I_D	-3.01	A
Pulsed Drain Current (Note 4)	I_{DM}	-35	A
Thermal Resistance – Junction-to-Ambient (Note 3)	$R_{\theta JA}$	166	$^{\circ}\text{C/W}$
Total Power Dissipation @ $T_A = 25^{\circ}\text{C}$	P_D	0.75	W
Continuous Drain Current @ $T_A = 25^{\circ}\text{C}$	I_D	-4.8	A
Continuous Drain Current @ $T_A = 70^{\circ}\text{C}$	I_D	-3.5	A
Maximum Operating Power Dissipation	P_D	0.2	W
Maximum Operating Drain Current	I_D	-2.48	A
Pulsed Drain Current (Note 4)	I_{DM}	-30	A
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^{\circ}\text{C}$
Single Pulse Drain-to-Source Avalanche Energy – Starting $T_J = 25^{\circ}\text{C}$ ($V_{DD} = -20$ Vdc, $V_{GS} = -5.0$ Vdc, Peak $I_L = -5.0$ Apk, $L = 40$ mH, $R_G = 25$ Ω)	E_{AS}	500	mJ
Maximum Lead Temperature for Soldering Purposes for 10 seconds	T_L	260	$^{\circ}\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

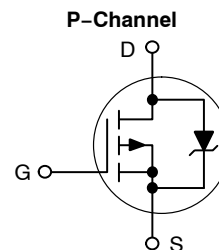
1. Mounted onto a 2" square FR-4 Board (1 in sq, 2 oz. Cu 0.06" thick single sided), $t = 10$ seconds.
2. Mounted onto a 2" square FR-4 Board (1 in sq, 2 oz. Cu 0.06" thick single sided), $t =$ steady state.
3. Minimum FR-4 or G-10 PCB, $t =$ steady state.
4. Pulse Test: Pulse Width = 300 μs , Duty Cycle = 2%.



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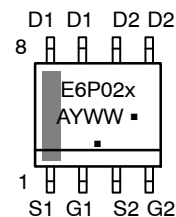
6 AMPERES, 20 VOLTS



MARKING DIAGRAM & PIN ASSIGNMENT



SOIC-8
CASE 751
STYLE 11



E6P02 = Specific Device Code
x = Blank or S
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NTMD6P02R2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel
NTMD6P02R2SG	SOIC-8 (Pb-Free)	2500 / Tape & Reel
NVMD6P02R2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D

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ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)*

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage (V _{GS} = 0 Vdc, I _D = -250 µAdc) Temperature Coefficient (Positive)	V _{(BR)DSS}	-20 -	- -11.6	- -	Vdc mV/°C
Zero Gate Voltage Drain Current (V _{DS} = -20 Vdc, V _{GS} = 0 Vdc, T _J = 25°C) (V _{DS} = -20 Vdc, V _{GS} = 0 Vdc, T _J = 70°C)	I _{DSS}	- -	- -	-1.0 -5.0	µAdc
Gate-Body Leakage Current (V _{GS} = -12 Vdc, V _{DS} = 0 Vdc)	I _{GSS}	-	-	-100	nAdc
Gate-Body Leakage Current (V _{GS} = +12 Vdc, V _{DS} = 0 Vdc)	I _{GSS}	-	-	100	nAdc

ON CHARACTERISTICS

Gate Threshold Voltage (V _{DS} = V _{GS} , I _D = -250 µAdc) Temperature Coefficient (Negative)	V _{GS(th)}	-0.6 -	-0.88 2.6	-1.20 -	Vdc mV/°C
Static Drain-to-Source On-State Resistance (V _{GS} = -4.5 Vdc, I _D = -6.2 Adc) (V _{GS} = -2.5 Vdc, I _D = -5.0 Adc) (V _{GS} = -2.5 Vdc, I _D = -3.1 Adc)	R _{DS(on)}	- - -	0.027 0.038 0.038	0.033 0.050 -	Ω
Forward Transconductance (V _{DS} = -10 Vdc, I _D = -6.2 Adc)	g _{FS}	-	15	-	Mhos

DYNAMIC CHARACTERISTICS

Input Capacitance	(V _{DS} = -16 Vdc, V _{GS} = 0 Vdc, f = 1.0 MHz)	C _{iss}	-	1380	1700	pF
Output Capacitance		C _{oss}	-	515	775	
Reverse Transfer Capacitance		C _{rss}	-	250	450	

SWITCHING CHARACTERISTICS (Notes 5 and 6)

Turn-On Delay Time	(V _{DD} = -10 Vdc, I _D = -1.0 Adc, V _{GS} = -10 Vdc, R _G = 6.0 Ω)	t _{d(on)}	-	15	25	ns
Rise Time		t _r	-	20	50	
Turn-Off Delay Time		t _{d(off)}	-	85	125	
Fall Time		t _f	-	50	110	
Turn-On Delay Time	(V _{DD} = -16 Vdc, I _D = -6.2 Adc, V _{GS} = -4.5 Vdc, R _G = 6.0 Ω)	t _{d(on)}	-	17	-	ns
Rise Time		t _r	-	65	-	
Turn-Off Delay Time		t _{d(off)}	-	50	-	
Fall Time		t _f	-	80	-	
Total Gate Charge	(V _{DS} = -16 Vdc, V _{GS} = -4.5 Vdc, I _D = -6.2 Adc)	Q _{tot}	-	20	35	nC
Gate-Source Charge		Q _{gs}	-	4.0	-	
Gate-Drain Charge		Q _{gd}	-	8.0	-	

BODY-DRAIN DIODE RATINGS (Note 5)

Diode Forward On-Voltage	(I _S = -1.7 Adc, V _{GS} = 0 Vdc) (I _S = -1.7 Adc, V _{GS} = 0 Vdc, T _J = 125°C)	V _{SD}	- -	-0.80 -0.65	-1.2 -	Vdc
Diode Forward On-Voltage	(I _S = -6.2 Adc, V _{GS} = 0 Vdc) (I _S = -6.2 Adc, V _{GS} = 0 Vdc, T _J = 125°C)	V _{SD}	- -	-0.95 -0.80	- -	Vdc
Reverse Recovery Time	(I _S = -1.7 Adc, V _{GS} = 0 Vdc, dI _S /dt = 100 A/µs)	t _{rr}	-	50	80	ns
		t _a	-	20	-	
		t _r	-	30	-	
Reverse Recovery Stored Charge		Q _{RR}	-	0.04	-	µC

5. Indicates Pulse Test: Pulse Width = 300 µs max, Duty Cycle = 2%.

6. Switching characteristics are independent of operating junction temperature.

*Handling precautions to protect against electrostatic discharge are mandatory.

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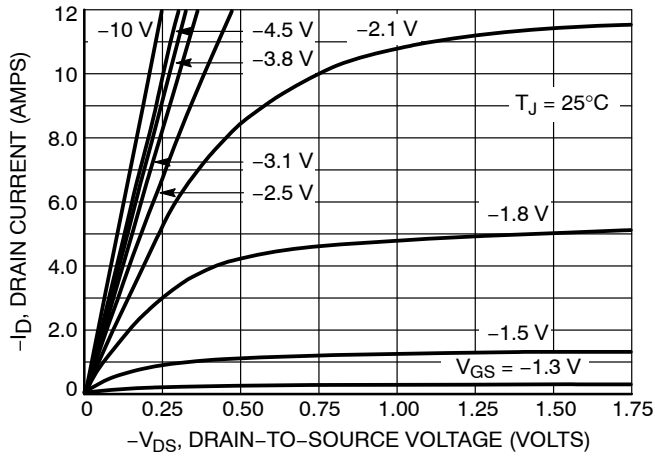


Figure 1. On-Region Characteristics

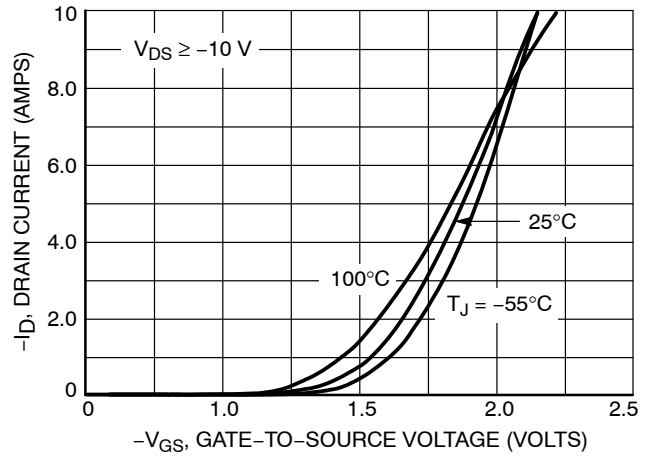


Figure 2. Transfer Characteristics

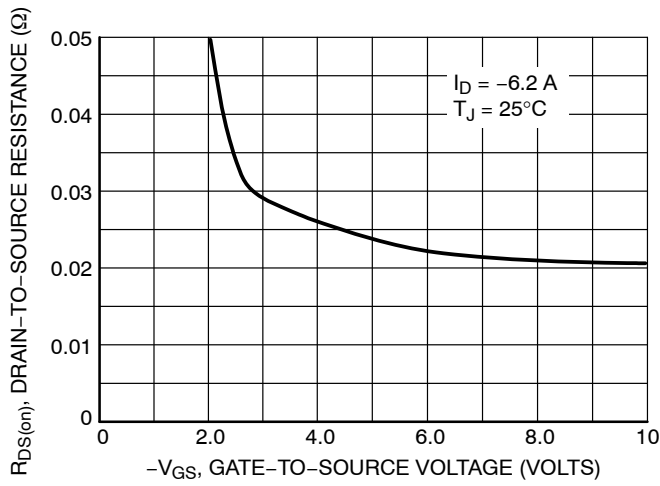


Figure 3. On-Resistance versus Gate-To-Source Voltage

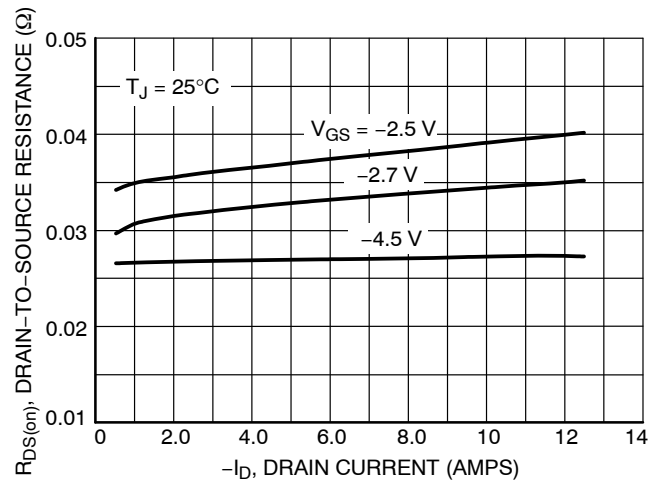


Figure 4. On-Resistance versus Drain Current and Gate Voltage

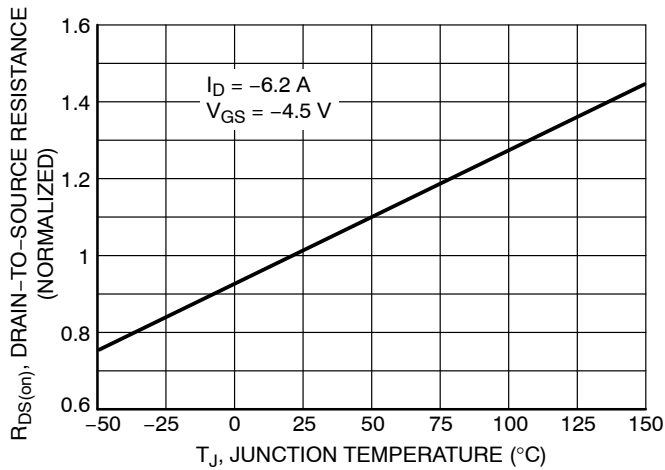


Figure 5. On-Resistance Variation with Temperature

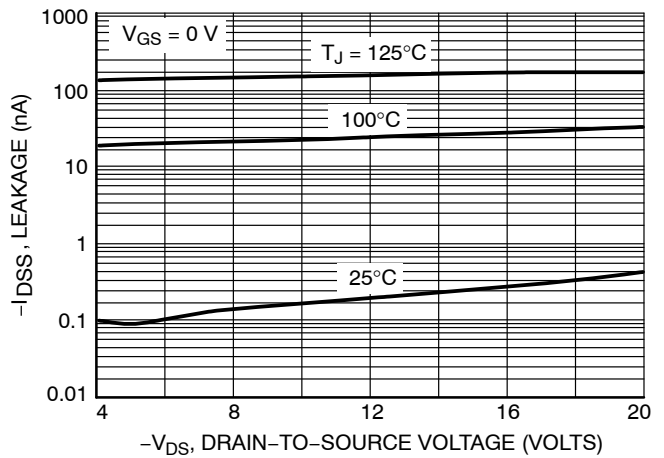


Figure 6. Drain-To-Source Leakage Current versus Voltage

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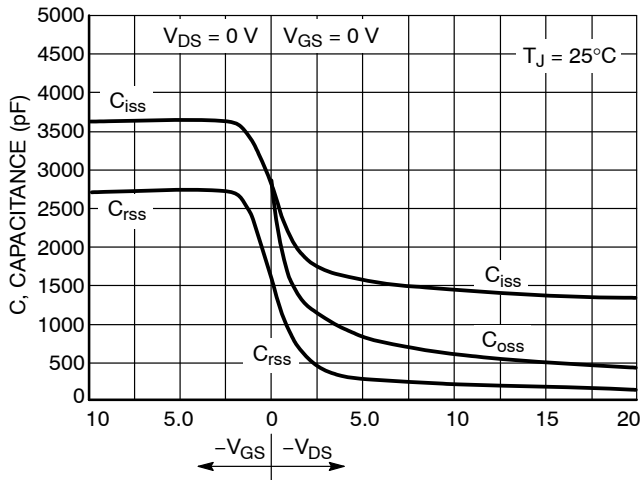


Figure 7. Capacitance Variation

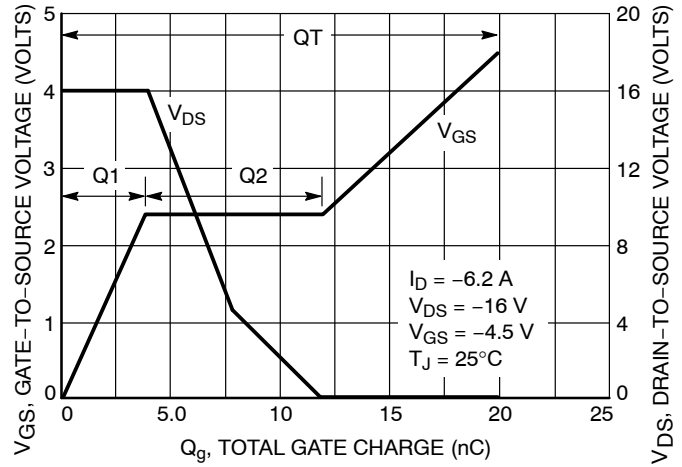


Figure 8. Gate-To-Source and Drain-To-Source Voltage versus Total Charge

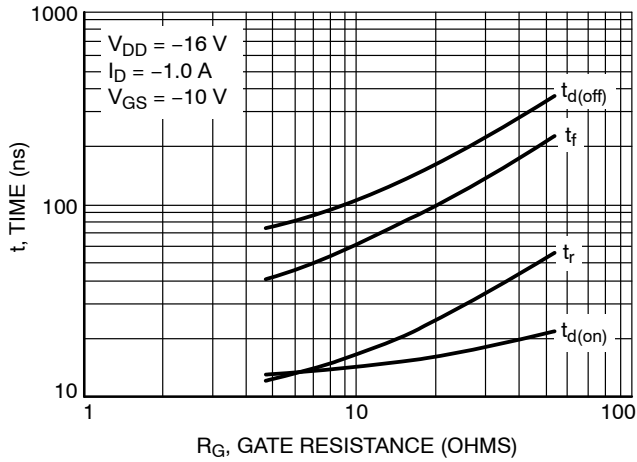


Figure 9. Resistive Switching Time Variation versus Gate Resistance

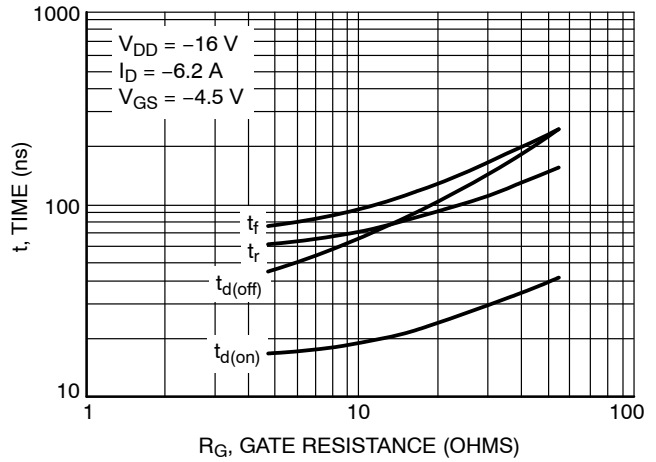


Figure 10. Resistive Switching Time Variation versus Gate Resistance

DRAIN-TO-SOURCE DIODE CHARACTERISTICS

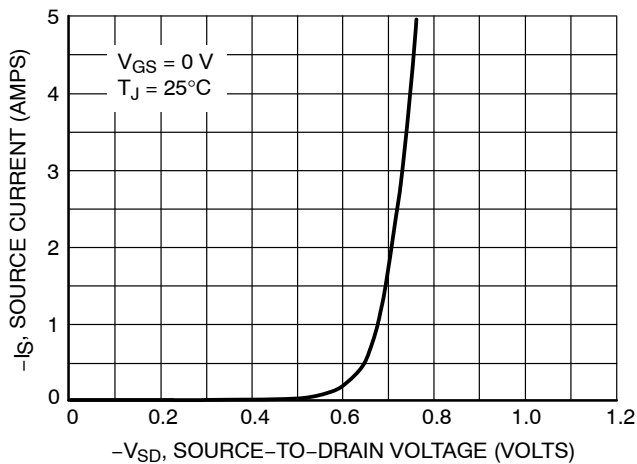


Figure 11. Diode Forward Voltage versus Current

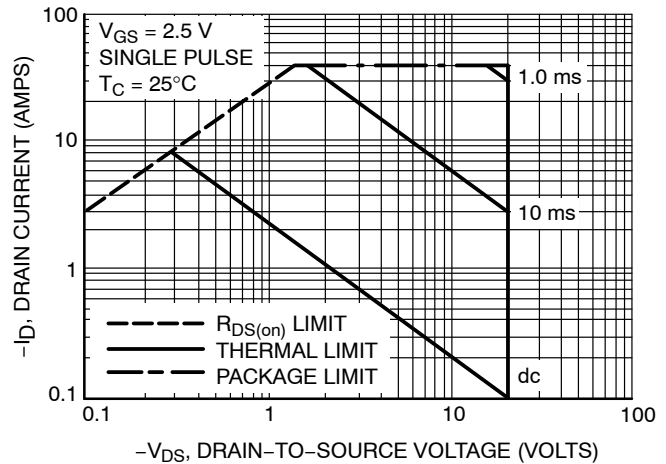


Figure 12. Maximum Rated Forward Biased Safe Operating Area

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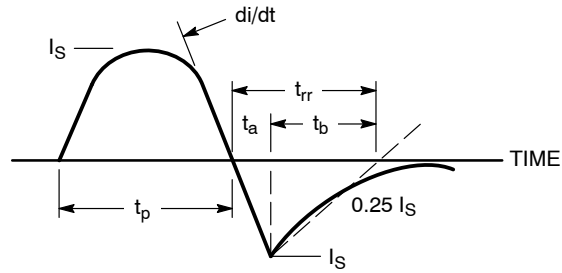


Figure 13. Diode Reverse Recovery Waveform

TYPICAL ELECTRICAL CHARACTERISTICS

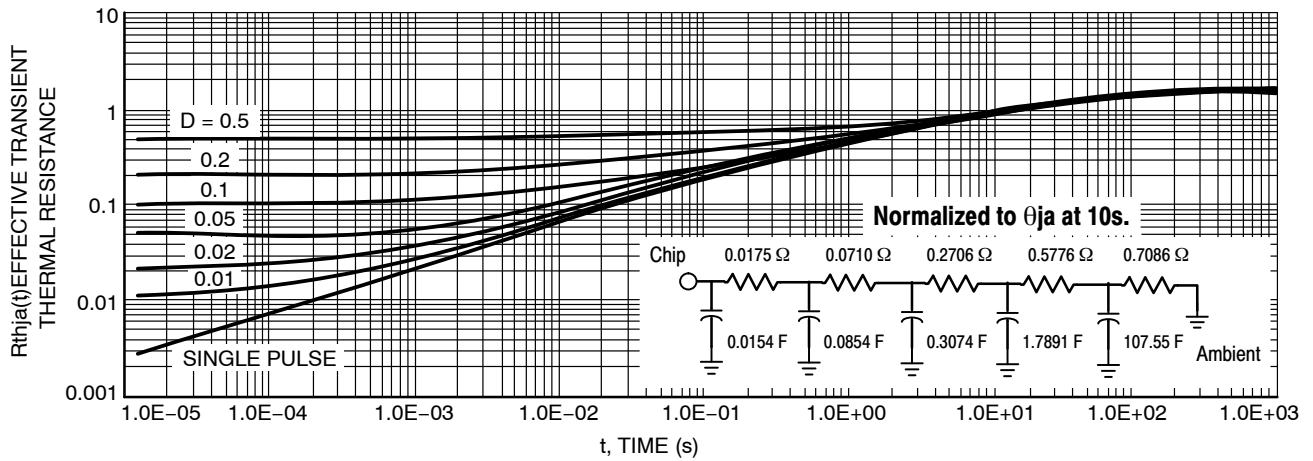


Figure 14. Thermal Response



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Электрон
Связь**

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